## Supplementary Information

## Influence of the covalent grafting of organic radicals to graphene on its magnetoresistance

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- SI 1. HR-TEM images.
- SI 2. Chemical Analysis.
- **SI 3.** EPR of unmodified graphene.
- SI 4. I-V conductivity versus voltage.
- SI 5. MR versus magnetic field.
- SI 6. MR versus magnetic field at variable temperature.
- SI 7. Resistance versus field for ethylmalonate molecules.
- **SI 8.** Fitting of the dependence of MR with the magnetic field at H>2T.

**SI 1.** HR-TEM images of (*top*) exfoliated graphene in oDCB (*left*) and **1-G** dispersed in ethanol (*right*), and (*bottom*) exfoliated graphene in benzylamine (*left*) and **1-G+** dispersed in ethanol (*right*). Insets display the Selected Area Electron Diffraction (SAED) collected for each sample that show the superposition of hexagonal diffraction patterns indicative of the presence of few-layers graphene.





(a)





(b)

	%C	%O	%N
Graphite	97.57	0.05	0.03
1-G	96.17	3.21	0.35
1-G+	93.78	5.64	0.58

SI 2. CHN analysis performed over pristine graphite, 1-G and 1-G+.

SI 3. EPR spectra at 300 K of unmodified graphene



SI 4. I-V conductivity versus voltage at room temperature of 1-G (green), 1-G+ (grey), 2-G (orange), exfoliated graphene in oDCB (light blue) and the mechanical mixture of graphite with 1 (black). In the bottom part, a table showing the conductivity values calculated from inverse of the slope of the I-V curves for the different samples in the ohmic region at very low voltages are summarized.



Sample	Conductivity [S·cm <sup>-1</sup> ]	Surface [cm <sup>2</sup> ]
1-G+	0.93	$1.77 \cdot 10^{-3}$
1-G	24.00	$1.87 \cdot 10^{-5}$
2-G	29.00	1.53·10 <sup>-5</sup>
Exfoliated G in oDCB	30.00	8.75·10 <sup>-5</sup>
Mechanical mixture of G and 1	28.22	$1.25 \cdot 10^{-4}$

**SI 5.** MR versus magnetic field at 300K of **1-G** (green), **1-G**+ (grey), **2-G** (orange) and exfoliated G in oDCB (blue). The three samples at 300 K show no differences between them at the low magnetic field part.



**SI 6.** MR versus magnetic field at different temperature of G-exfoliated in oDCB (left), **2-G** (right)). The bottom panel shows a zoom-in of the low field area for lower and higher temperature with the appearance of an anti-localization effect at 2 K. The LFMR effect present in 1-G and 1-G+ is not observed for any of them.



**SI 7.** Resistance versus field for ethylmalonate molecules. As describen in the text, no MR signal was observed.



**SI 8**. MR versus magnetic field at magnetics fields higher than 2 T were fitted with the following expressions MR(H)=  $a \cdot H + b \cdot H^2$ , considering both linear and quadratic dependence.<sup>2, 3a</sup>



As observed, the MR behavior at high fields is quite similar for all samples. In fact, all of them exhibit a non-saturating MR as expected for graphene-based materials.<sup>1</sup> In this high field area, for graphene two contributions are usually present. The first one in due to the curving of electron trajectories in the graphene plane which usually results in a positive MR with quadratic magnetic field dependence MR~  $(\mu \cdot \mu_0 \cdot H)^2$ .<sup>1a, 2</sup> The second one is a linear MR, which has been observed in many systems.<sup>3</sup> Abrikosov gave with a quantum description for a zero band-gap system to explain the linear MR behavior.<sup>4</sup> Here, all the experimental data have been fitted with the equation proposed in reference 1a:

$$MR(H) = R(H)/R(0) - 1 = \rho H + ((\mu \cdot \mu_0 \cdot H)^2)$$

where the MR is proportional to a linear plus a quadratic magnetic field dependence, and where  $\mu_0$  is the permeability in vacuum and  $\rho$  is the proportional coefficient.

As a parameter the  $\mu$  the carrier mobility is obtained from the curve fitting. The calculated carrier mobility is 141 cm<sup>2</sup>·V·s for the exfoliated graphene at 2 K, and the criterion  $\mu(\mu_0 \cdot H) < 1$  is satisfied for the quadratic MR. The lower values for carrier mobility  $\mu$  may be very low due

<sup>&</sup>lt;sup>1</sup> a) Z-M. Liao, H-C. Wu, S. Kumar, G.S. Duesberg, Y-B. Zhou, G.L.W. Cross, I. V. Shvets, D-P. Yu, *Adv. Mater.*,2012, **24**, 1862. b) E. McCann, K. Kechedzhi, V.I. Fal'ko, H. Suzuura, T. Ando, B.L. Altshuler, *Phys. Rev. Lett.* 2006, **97**, 146805

<sup>&</sup>lt;sup>2</sup> J. L. Olsen, Electron Transport in Metals, Interscience, New York 1962

<sup>&</sup>lt;sup>3</sup> A.L. Friedman, J.L. Tedesco, P.M. Cambell, J.C. Culberstson, E. Aifer, F. K. Perkins, R.L.

Myers-Ward, J. K. Hite, C.R. Eddy Jr., G.G. Jenirgan, D.K. Gaskill, *Nat. Nanotechnol.* 2008, **3**, 408.

<sup>&</sup>lt;sup>4</sup> A.A.Abrikosov, P.B. Littlewood, *Nature*, 2003, **426**, 162

to the existence of boundaries, defects and impurities. The calculated carrier mobility for the rest is lower as one can expected because the impurities and the defects increase.